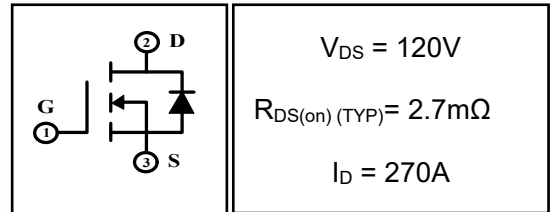


270A 120V N-channel Enhancement Mode Power MOSFET

1 Description

This N-channel enhancement mode power MOSFET utilizes advanced Split Gate Trench technology, which provides excellent $R_{DS(on)}$ and low Gate charge at the same time. Which accords with the RoHS standard.

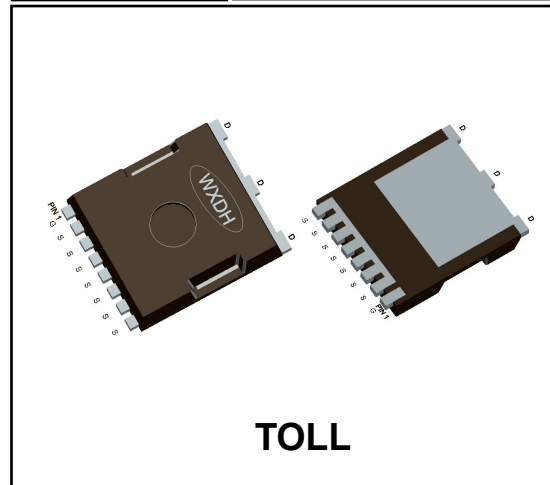


2 Features

- Low on resistance
- Low gate charge
- Fast switching
- Low reverse transfer capacitances
- 100% single pulse avalanche energy test
- 100% ΔV_{DS} test

3 Applications

- Synchronous rectification in SMPS
- Motor control and drive
- Battery management
- UPS
- Power tools



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter		Symbol	Rating	Units
Drain-to-Source Voltage		V_{DSS}	120	V
Gate-to-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	$T_C=25^\circ C$	I_D	270	A
	$T_C=100^\circ C$		171	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	1080	A
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	1482	mJ
Power Dissipation	$T_a=25^\circ C$	P_{tot}	2.5	W
	$T_C=25^\circ C$	P_{tot}	417	W
Junction Temperature Range		T_j	-55~150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

4.2 Thermal Characteristics

Parameter	Symbol	Value			Units
		Min	Typ	Max	
Thermal Resistance, Junction to Case-sink	R_{thJC}	---	0.3	0.4	$^\circ C/W$
Thermal Resistance, Junction to Ambient	R_{thJA}	---	38	50	$^\circ C/W$

4.3 Electrical Characteristics (Tc=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			Min	Typ	Max	
Off Characteristics						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	120	--	--	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=120V, V_{GS}=0V, T_C=25^\circ C$	--	--	1	μA
		$V_{DS}=120V, V_{GS}=0V, T_C=125$	--	--	100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-to-Source on-state Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=60A$	--	2.7	3.2	m Ω
Transconductance	G_{fs}	$V_{DS}=5V, I_D=60A$	--	124	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=60V, f=1.0MHz$	--	8592	--	pF
Output Capacitance	C_{oss}		--	1011	--	
Reverse Transfer Capacitance	C_{rss}		--	24	--	
Gate Resisitance	R_G	$V_{DS}=0V, V_{GS}=0V, F=1MHz$	--	0.9	--	Ω
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=60V, I_D=100A, R_G=3\Omega$	--	37	--	nS
Turn-on Rise Time	t_r		--	112	--	
Turn-off Delay Time	$t_{d(off)}$		--	55	--	
Turn-off Fall Time	t_f		--	99	--	
Total Gate Charge	Q_g	$I_D=100A, V_{DS}=60V, V_{GS}=10V$	--	105	--	nC
Gate-to-Source Charge	Q_{gs}		--	40.5	--	
Gate-to-Drain("Miller") Charge	Q_{gd}		--	20.7	--	
Gate plateau voltage	$V_{plateau}$		--	5.5	--	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V_{SD}	$V_{GS}=0V, I_S=60A$	--	--	1.4	V
Diode Forward Current	I_S		--	--	270	A
Reverse Recovery Time(3)	t_{rr}	$T_J=25^\circ C, I_F=60A$	--	82	--	nS
Reverse Recovery Charge(3)	Q_{rr}	$dI_F/dt=100A/\mu S, V_{GS}=0V$	--	136	--	nC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, $t \leq 10sec$.
- 3: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4: $L=0.5mH, V_{DD}=80V, V_G=120V, Start T_J=25^\circ C$.

5 Typical characteristics diagrams

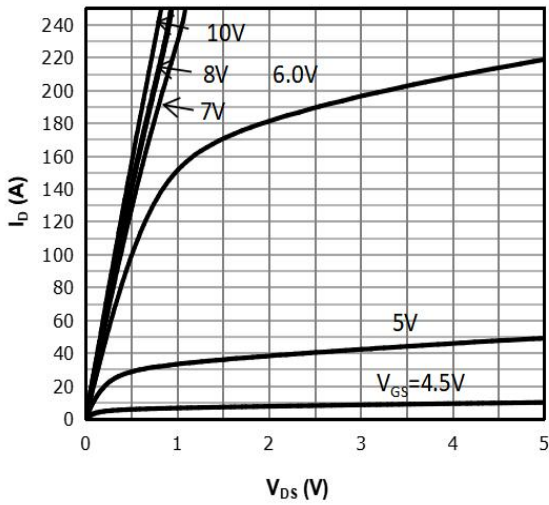


Fig 1 Output Characteristics

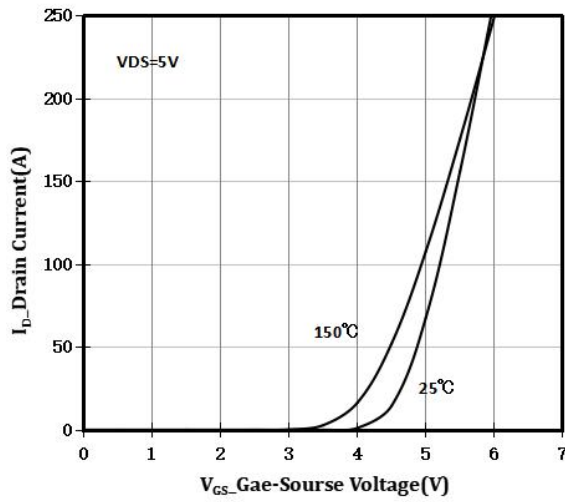


Fig 2 Transfer Characteristics

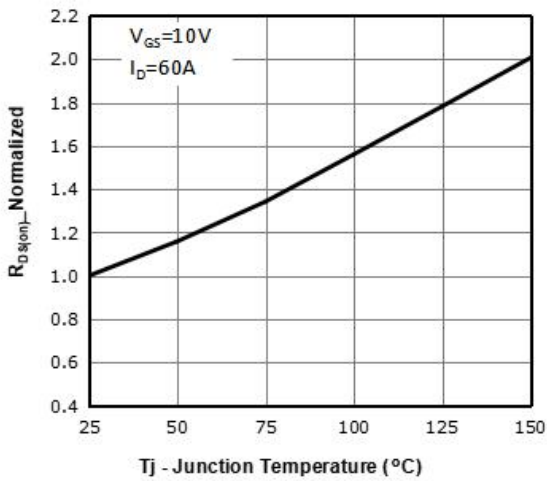


Fig 3 RDSON vs Junction Temperature

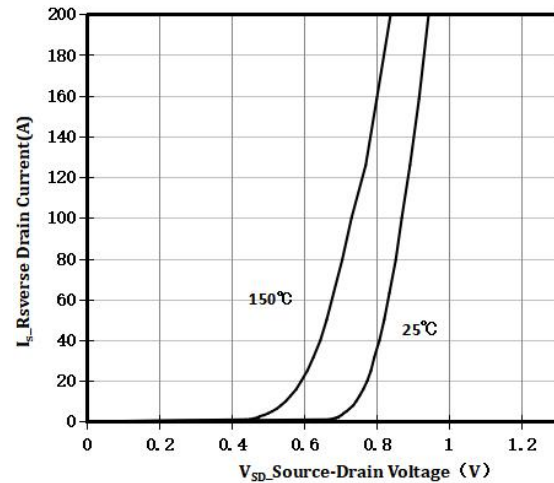


Fig 4 VSD Source-Drain Diode forward

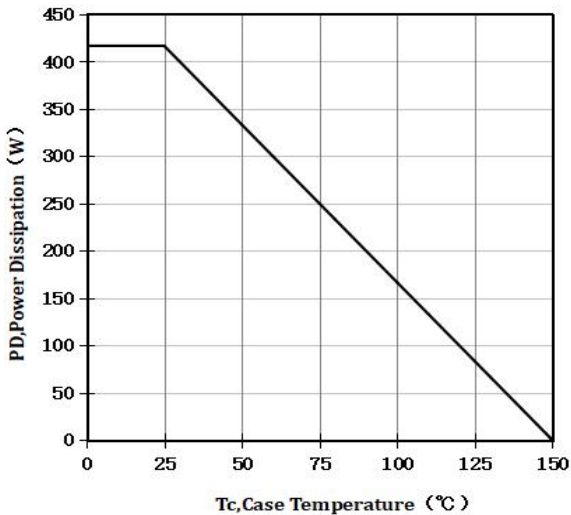


Fig 5 Power De-rating

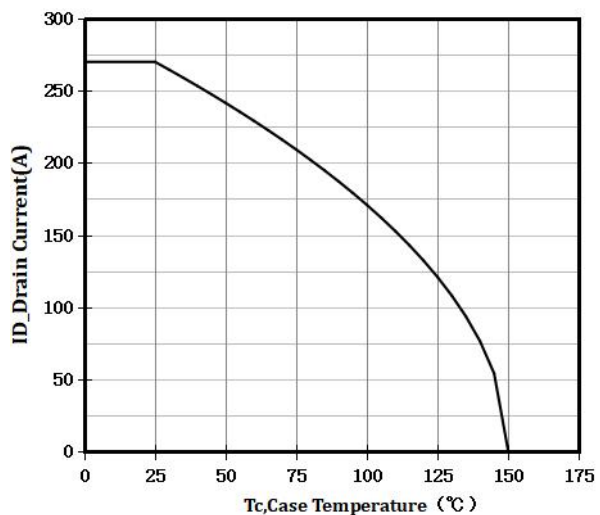


Fig 6 ID Current De-rating

5 Typical characteristics diagrams(continues)

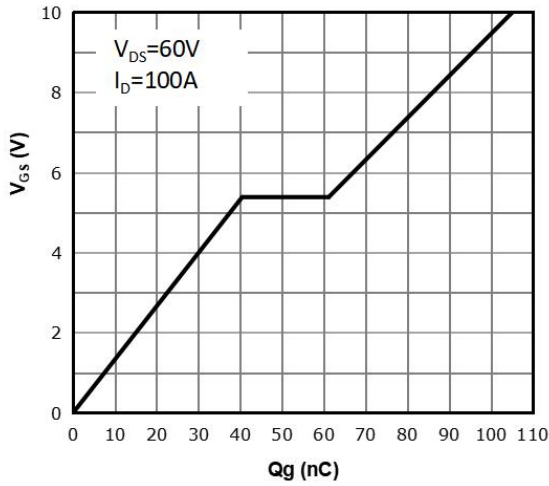


Fig 7 Gate Charge Figure

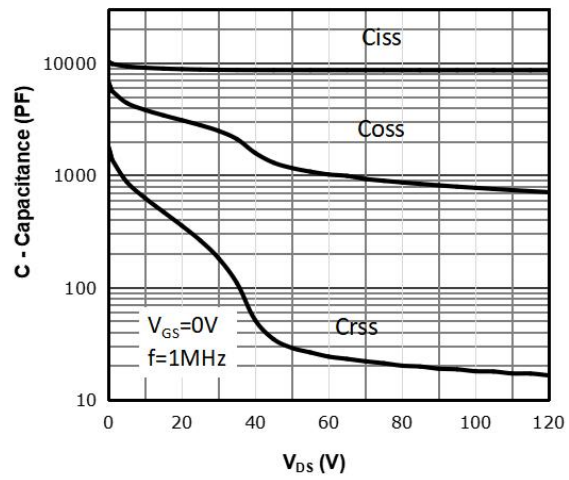


Fig 8 Capacitance vs Vds

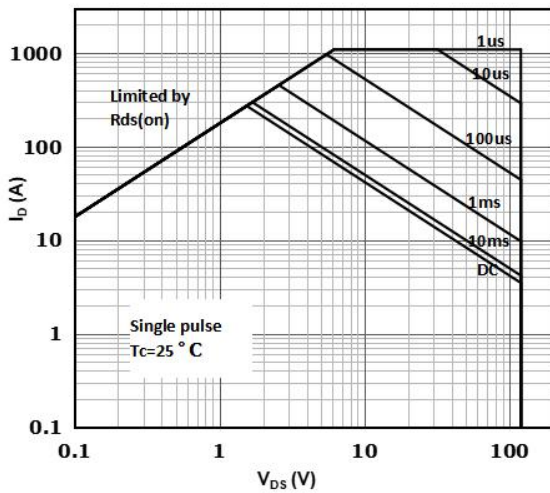


Fig 9 Safe Operation Area

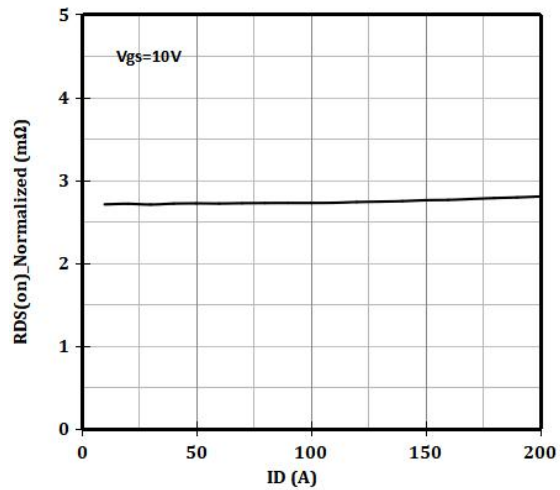


Fig 10 RDSON vs Drain Current

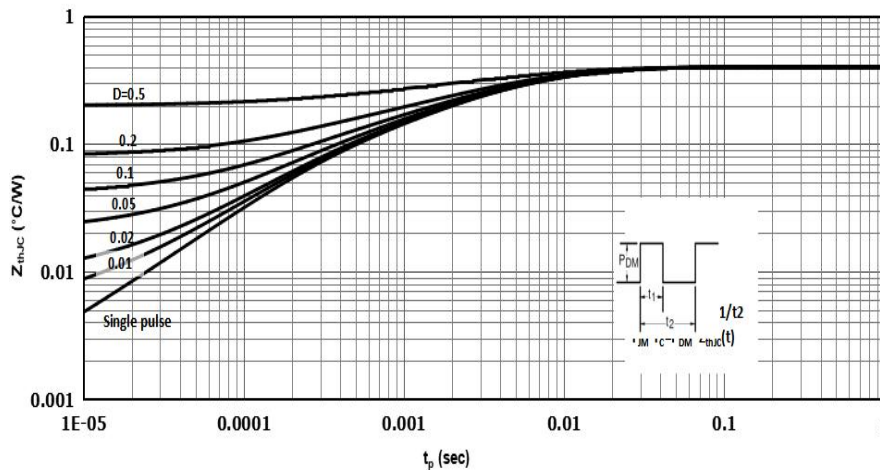
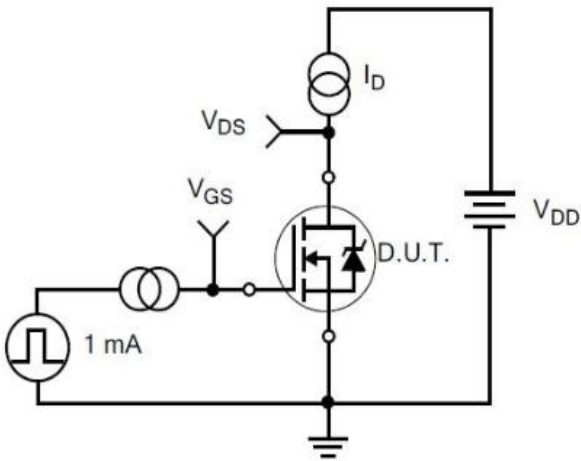
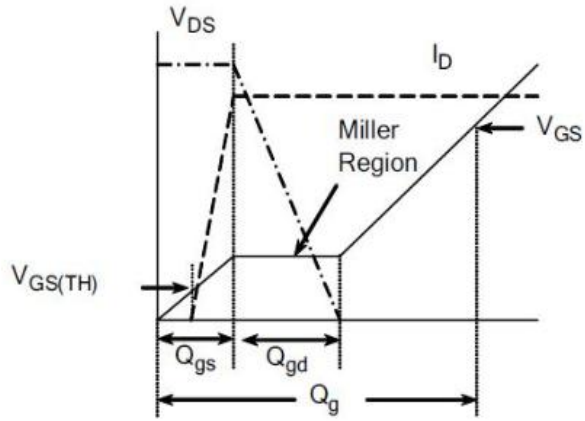


Fig 11 Normalized Maximum Transient Thermal Impedance

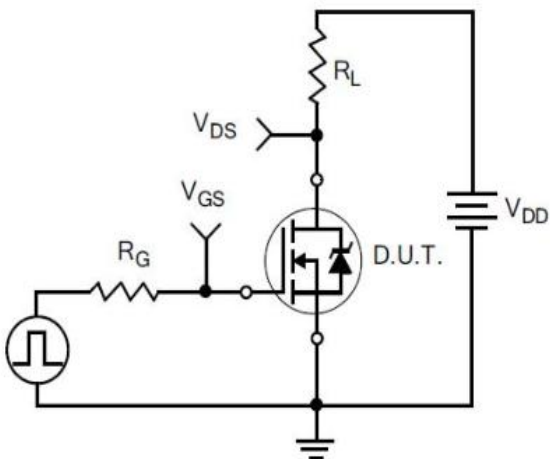
6 Typical Test Circuit and Waveform



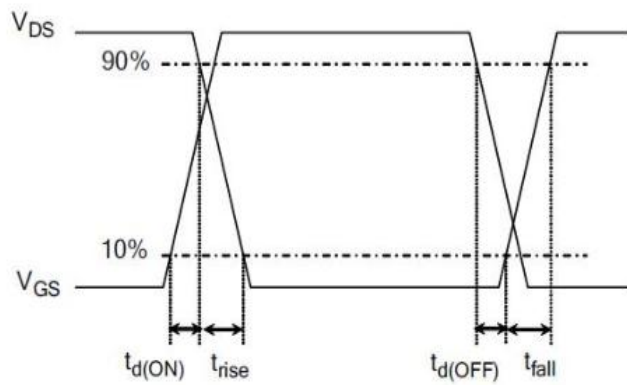
1) Gate Charge Test Circuit



2) . Gate Charge Waveform

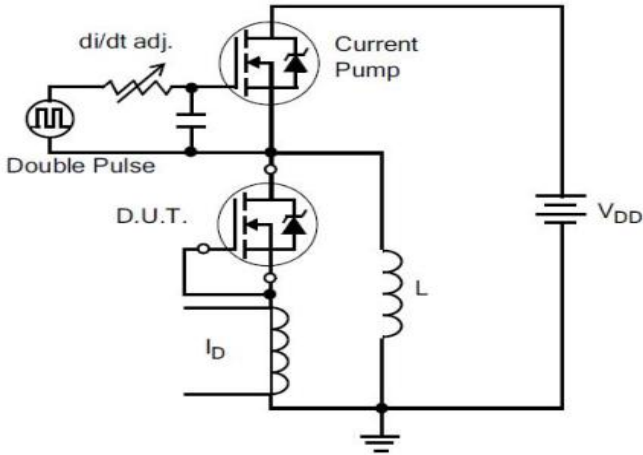


3) Resistive Switching Test Circuit

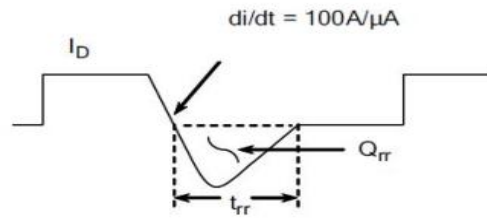


4) Resistive Switching Waveforms

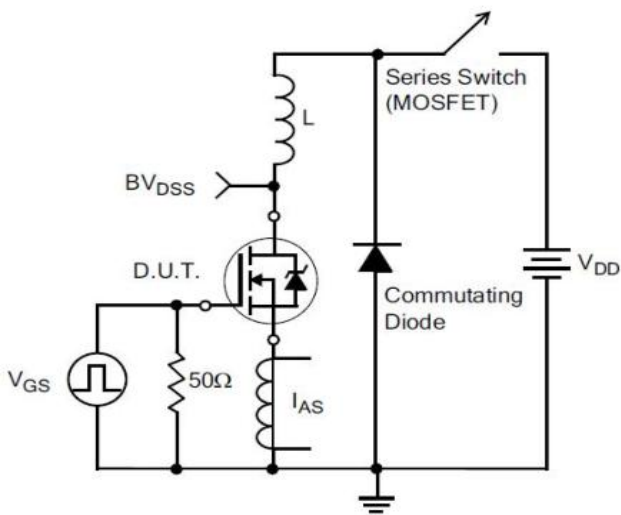
6 Typical Test Circuit and Waveform(continues)



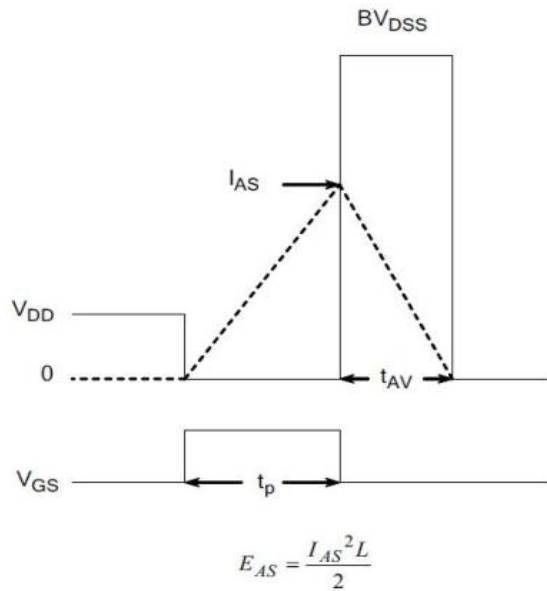
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

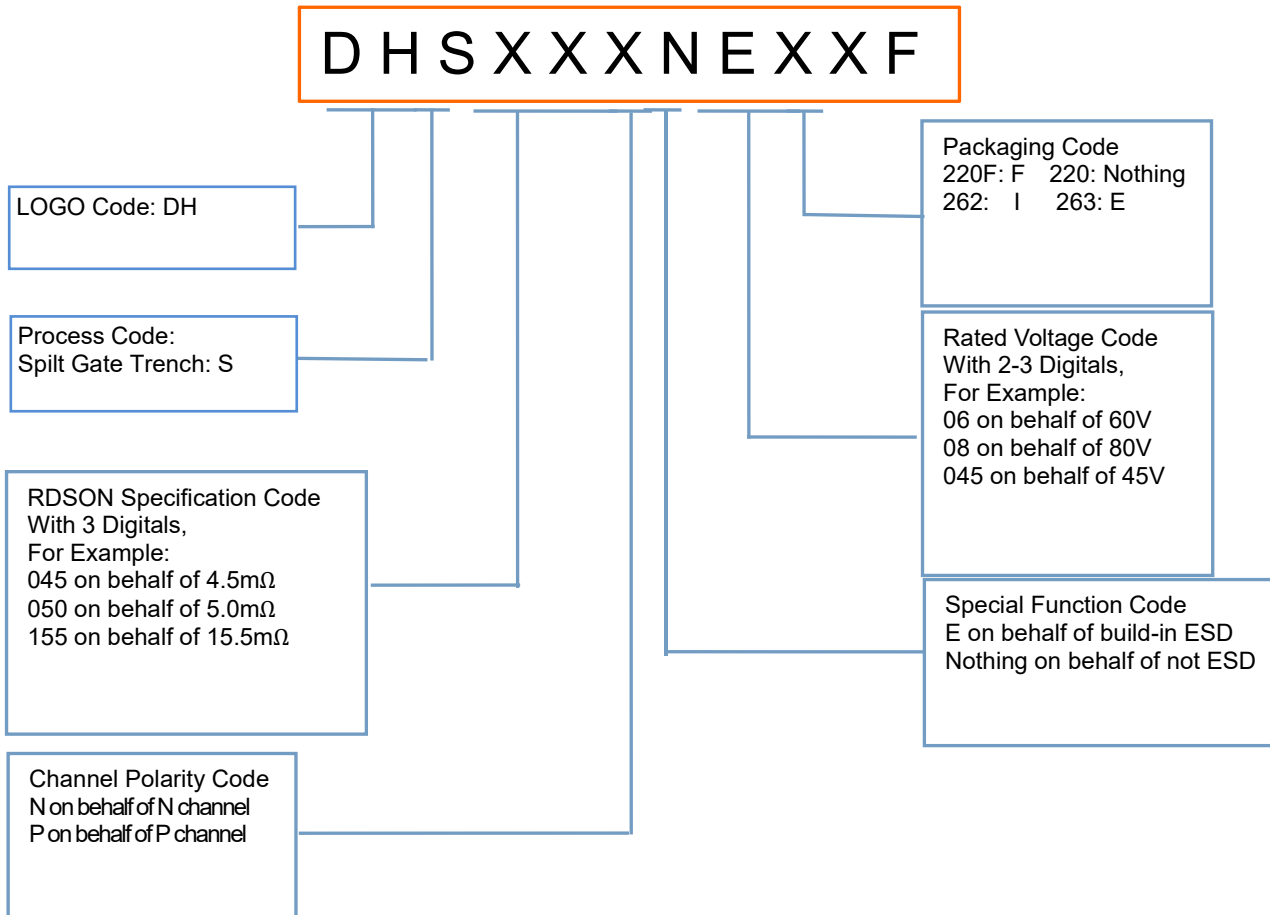


7) . Unclamped Inductive Switching Test Circuit



8) Unclamped Inductive Switching Waveforms

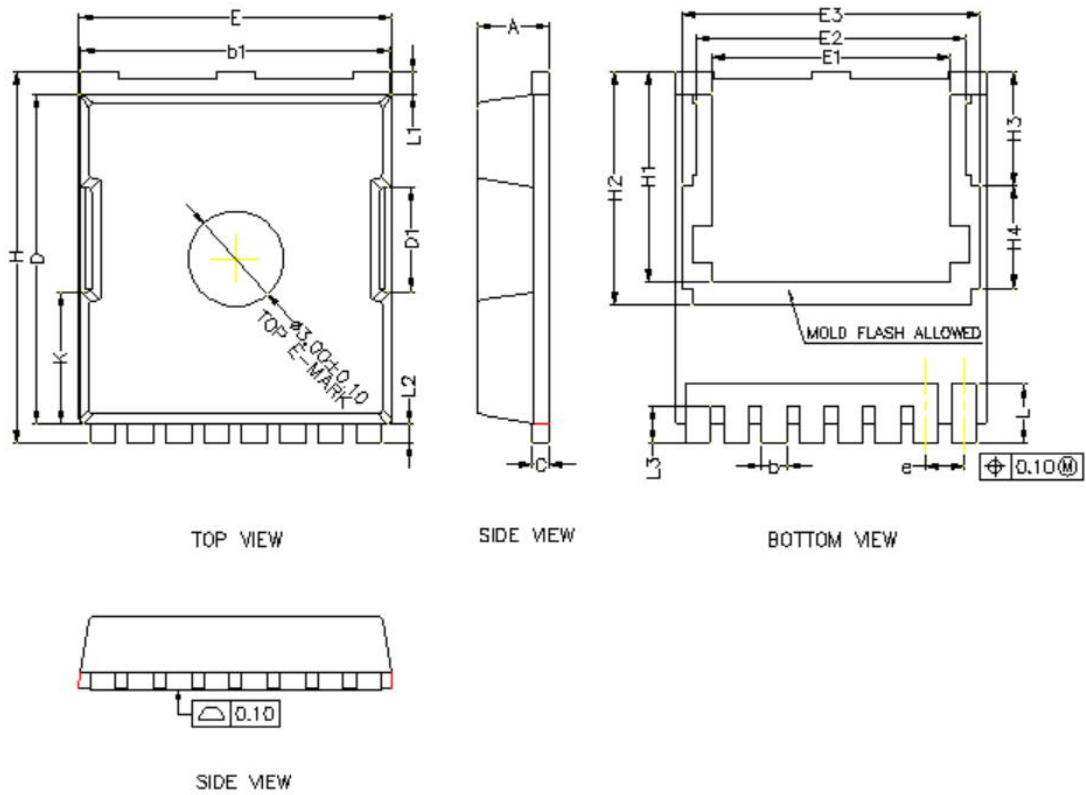
7 Product Names Rules



8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
DHS044N12U	TOLL	DHS044N12U	Pb-free	Tape & Reel	1800/box

9 Dimensions



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
c	0.40	0.50	0.60
D	10.28	10.43	10.58
D1	3.15	3.30	3.45
E	9.70	9.90	10.10
E1	7.35	7.50	7.65
E2	8.35	8.50	8.65
E3	9.31	9.46	9.61
e	1.10	1.20	1.30
H	11.48	11.73	11.88
H1	6.55	6.65	6.75
H2	7.20	7.35	7.50
H3	3.44	3.59	3.74
H4	3.11	3.26	3.41
K	4.03	4.18	4.33
L	1.60	1.85	2.10
L1	0.55	0.70	0.85
L2	0.45	0.60	0.75
L3	1.00	1.15	1.30

10 Attentions

- Jiangsu Donghai Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Donghai products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2023.01.09	1.0	Original	9
2023.01.12	2.0	Modified	1,2,3,4